



STD1NK60 - STD1NK60-1 STQ1HNK60R

N-CHANNEL 600V - 8Ω - 1A DPAK / IPAK / TO-92
SuperMESH™ Power MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D	P _w
STD1NK60	600 V	< 8.5 Ω	1 A	30 W
STD1NK60-1	600 V	< 8.5 Ω	1 A	30 W
STQ1HNK60R	600 V	< 8.5 Ω	0.4 A	3 W

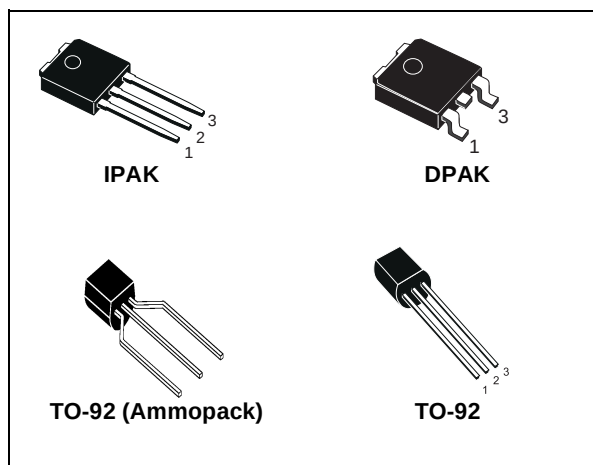
- TYPICAL R_{DS(on)} = 8 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- NEW HIGH VOLTAGE BENCHMARK

DESCRIPTION

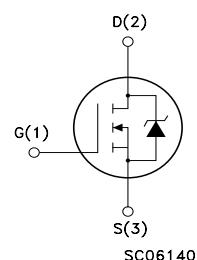
The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

APPLICATIONS

- SWITCH MODE LOW POWER SUPPLIES (SMPS)
- LOW POWER, LOW COST CFL (COMPACT FLUORESCENT LAMPS)
- LOW POWER BATTERY CHARGERS



INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STD1NK60T4	D1NK60	DPAK	TAPE & REEL
STD1NK60-1	D1NK60	IPAK	TUBE
STQ1HNK60R	1HNK60R	TO-92	BULK
STQ1HNK60R-AP	1HNK60R	TO-92	AMMOPAK

STD1NK60 - STD1NK60-1 - STQ1HNK60R

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STD1NK60 STD1NK60-1	STQ1HNK60R	
V_{DS}	Drain-source Voltage ($V_{GS} = 0$)	600		V
V_{DGR}	Drain-gate Voltage ($R_{GS} = 20\text{ k}\Omega$)	600		V
V_{GS}	Gate- source Voltage	± 30		V
I_D	Drain Current (continuous) at $T_C = 25^\circ\text{C}$	1.0	0.4	A
I_D	Drain Current (continuous) at $T_C = 100^\circ\text{C}$	0.63	0.25	A
$I_{DM}(\bullet)$	Drain Current (pulsed)	4	1.6	A
P_{TOT}	Total Dissipation at $T_C = 25^\circ\text{C}$	30	3	W
	Derating Factor	0.24	0.025	W/ $^\circ\text{C}$
$dv/dt(1)$	Peak Diode Recovery voltage slope	3		V/ns
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150		$^\circ\text{C}$

(●) Pulse width limited by safe operating area

(1) $I_{SD} \leq 1.0\text{A}$, $di/dt \leq 100\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$.

THERMAL DATA

		DPAK / IPAK	TO-92	
$R_{thj-case}$	Thermal Resistance Junction-case Max	4.16		$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Junction-ambient Max	100	120	$^\circ\text{C}/\text{W}$
$R_{thj-lead}$	Thermal Resistance Junction-lead Max		40	$^\circ\text{C}/\text{W}$
T_l	Maximum Lead Temperature For Soldering Purpose	275	260	$^\circ\text{C}$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value		Unit
		DPAK / IPAK	TO-92	
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	1		A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	25		mJ

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}C$ UNLESS OTHERWISE SPECIFIED)
ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 1 \text{ mA}$, $V_{GS} = 0$	600			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$, $T_C = 125^{\circ}C$			1 50	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 30V$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	2.25	3	3.7	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V$, $I_D = 0.5 \text{ A}$		8	8.5	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (1)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$, $I_D = 0.5 \text{ A}$		1		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25V$, $f = 1 \text{ MHz}$, $V_{GS} = 0$		156 23.5 3.8		pF pF pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 300 \text{ V}$, $I_D = 0.5 \text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3)		6.5 5		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 480V$, $I_D = 1.0 \text{ A}$, $V_{GS} = 10V$, $R_G = 4.7\Omega$		7 1.1 3.4	10	nC nC nC

SWITCHING OFF

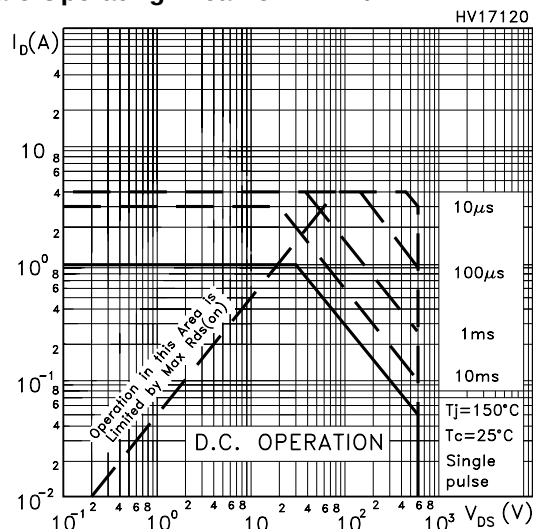
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 300 \text{ V}$, $I_D = 0.5 \text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3)		19 25		ns ns
$t_r(V_{off})$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 480V$, $I_D = 1.0 \text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10V$ (Inductive Load see, Figure 5)		24 25 44		ns ns ns

SOURCE DRAIN DIODE

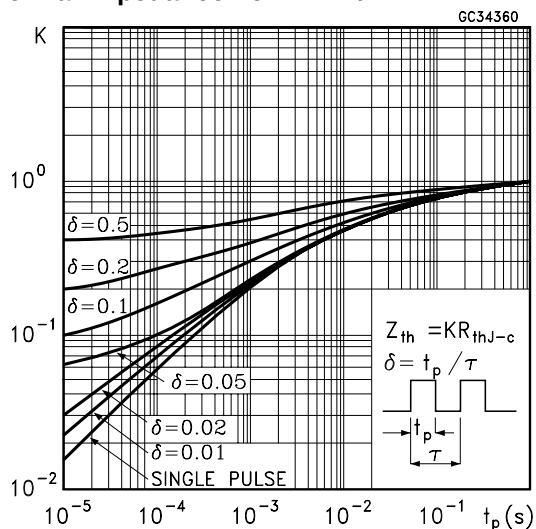
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (2)$	Source-drain Current Source-drain Current (pulsed)				1 4	A A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 1.0 \text{ A}$, $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 1.0 \text{ A}$, $di/dt = 100A/\mu s$ $V_{DD} = 25V$, $T_J = 150^{\circ}C$ (see test circuit, Figure 5)		229 377 3.3		ns μC A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

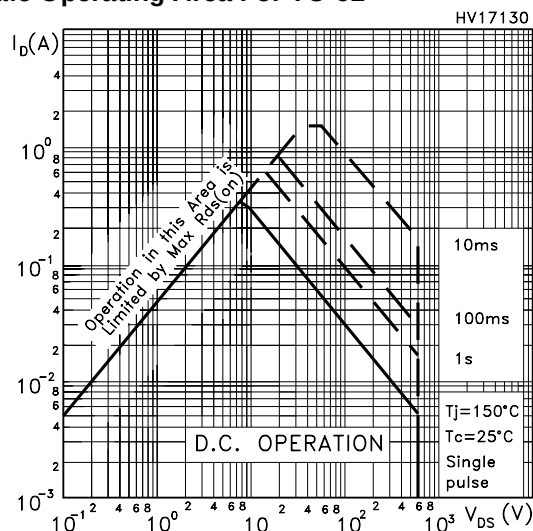
Safe Operating Area For DPAK/IPAK



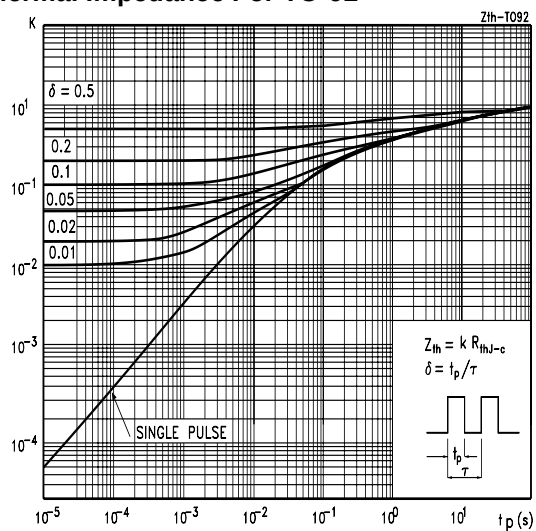
Thermal Impedance For DPAK/IPAK



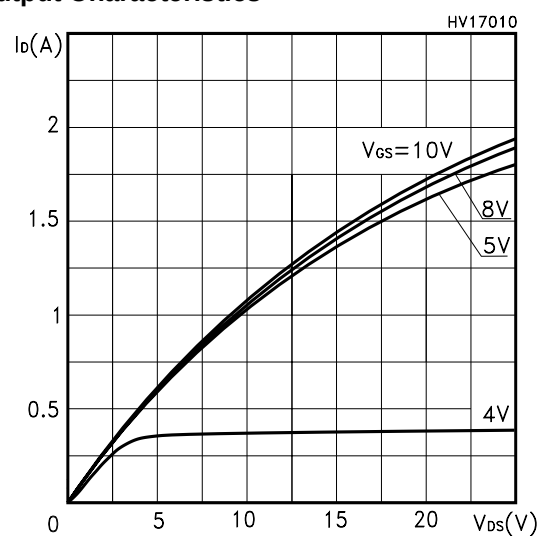
Safe Operating Area For TO-92



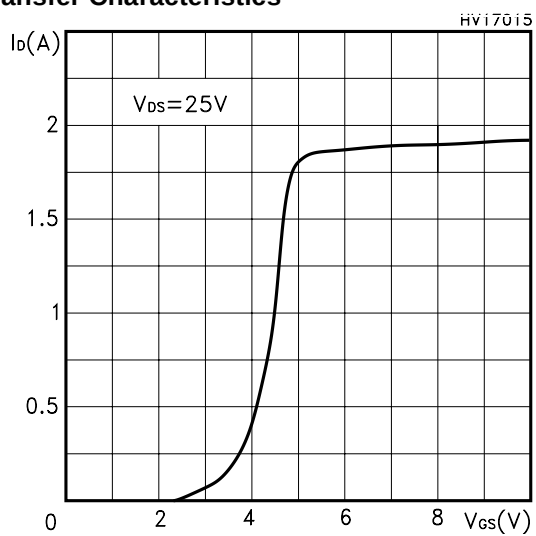
Thermal Impedance For TO-92



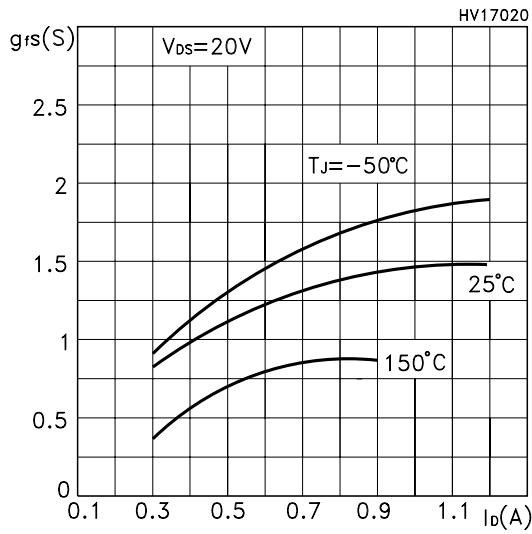
Output Characteristics



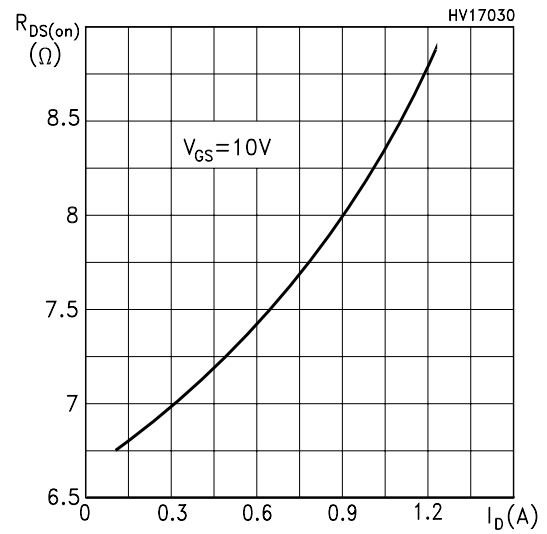
Transfer Characteristics



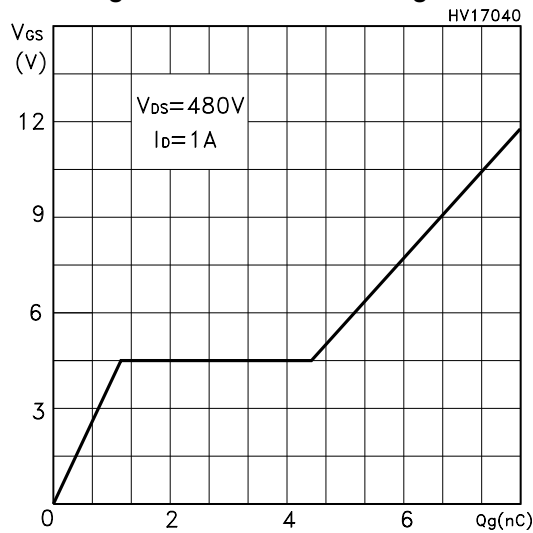
Transconductance



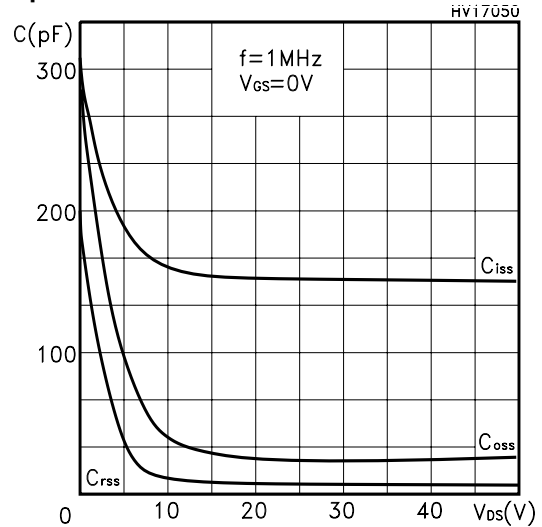
Static Drain-source On Resistance



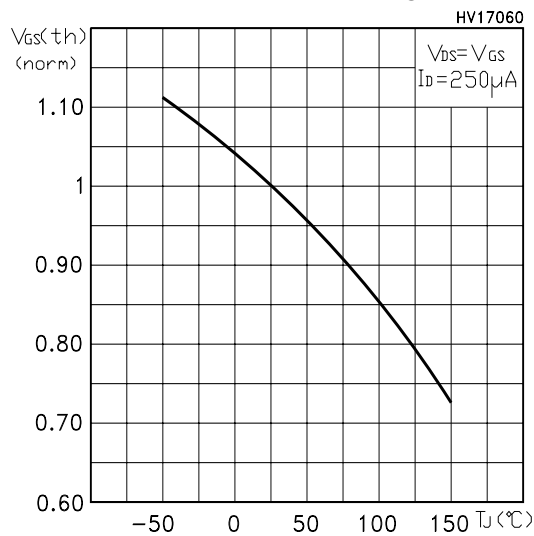
Gate Charge vs Gate-source Voltage



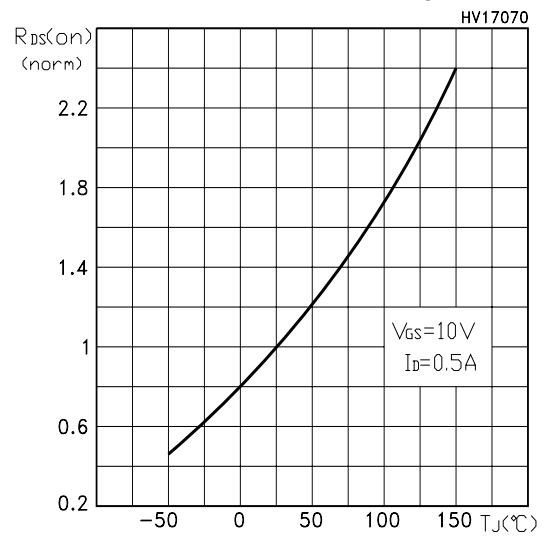
Capacitance Variations



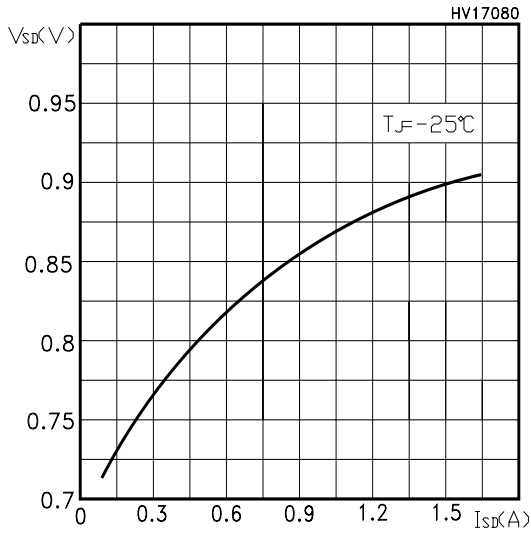
Normalized Gate Threshold Voltage vs Temp.



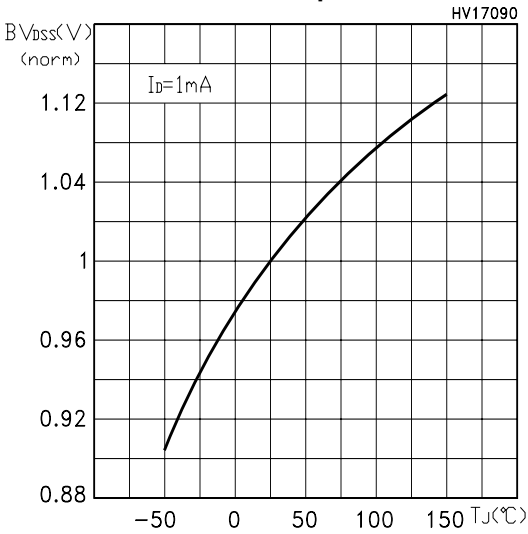
Normalized On Resistance vs Temperature



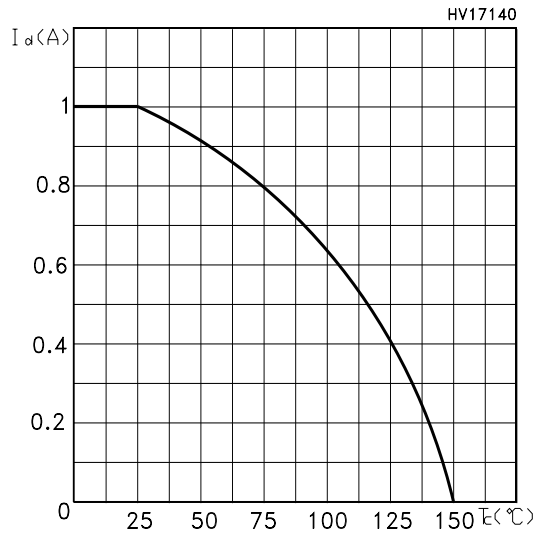
Source-drain Diode Forward Characteristics



Normalized BVDSS vs Temperature



Max Id Current vs Tc



Maximum Avalanche Energy vs Temperature

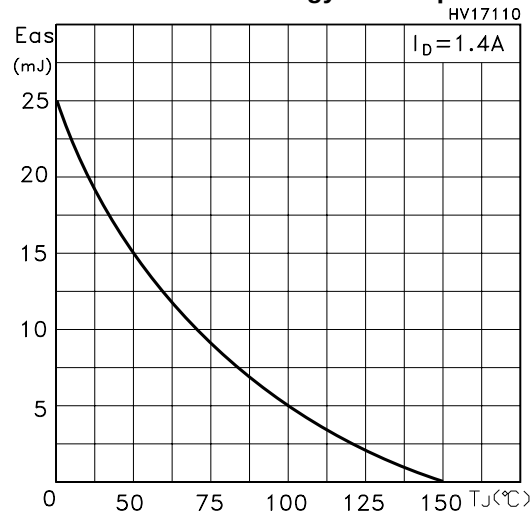


Fig. 1: Unclamped Inductive Load Test Circuit

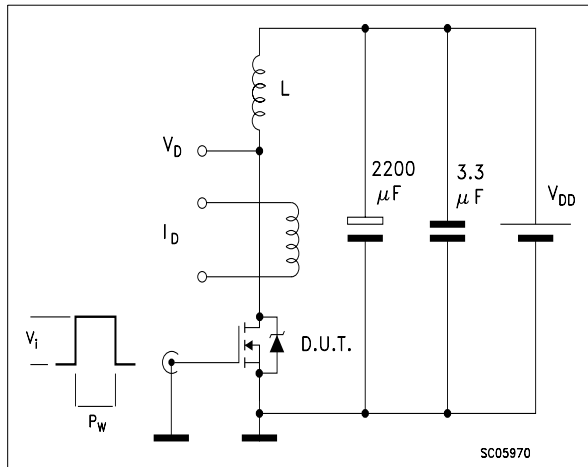


Fig. 2: Unclamped Inductive Waveform

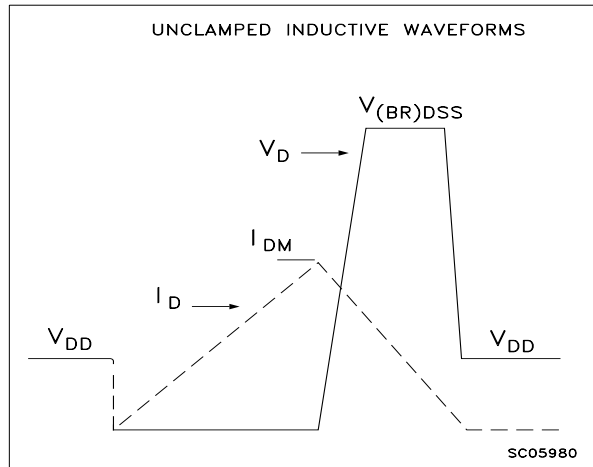


Fig. 3: Switching Times Test Circuit For Resistive Load

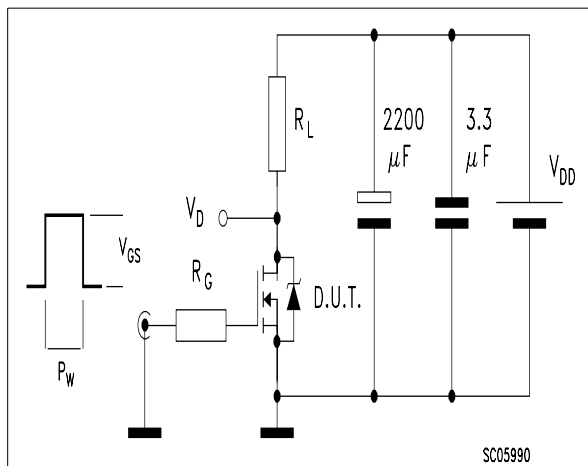


Fig. 4: Gate Charge test Circuit

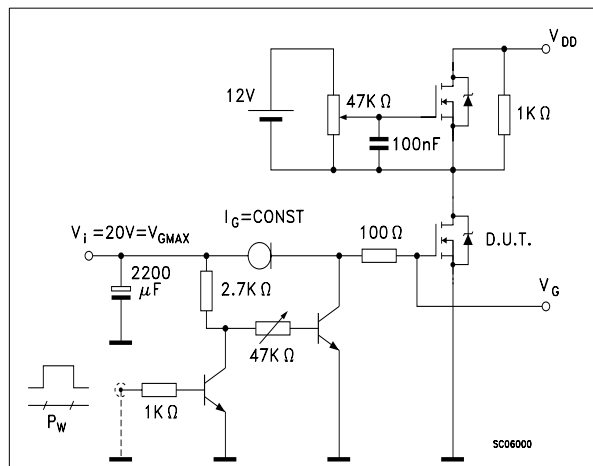
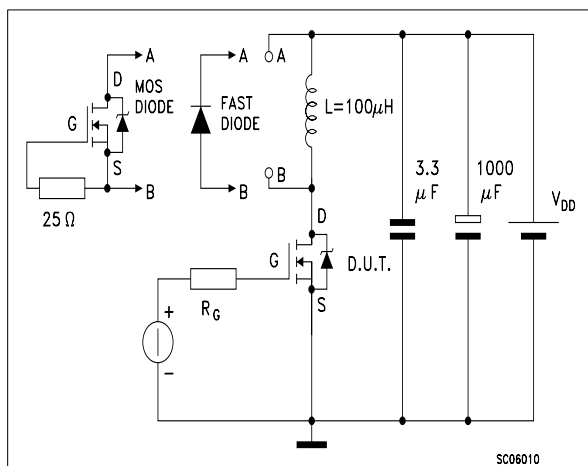
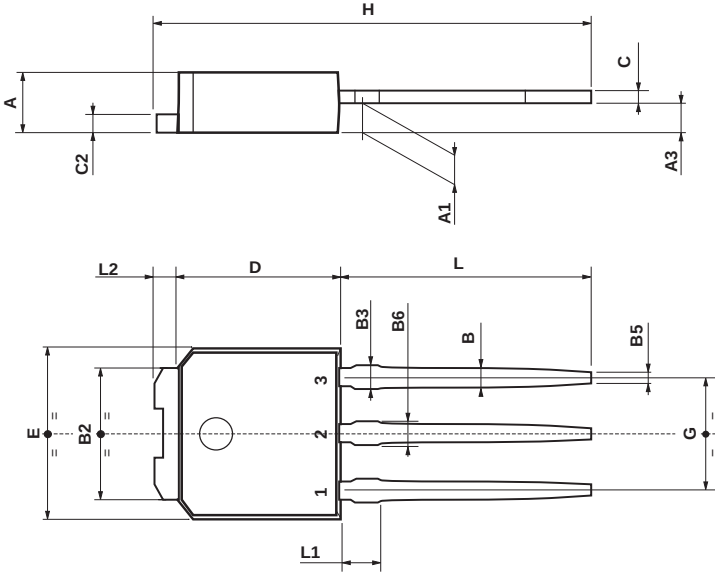


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-251 (IPAK) MECHANICAL DATA

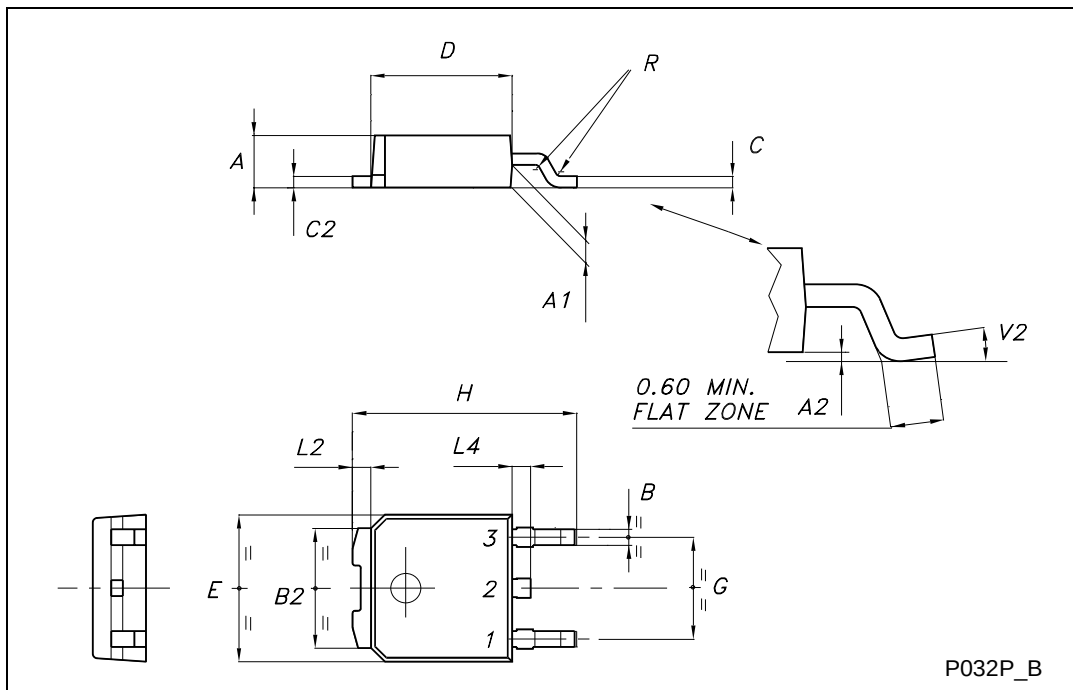
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



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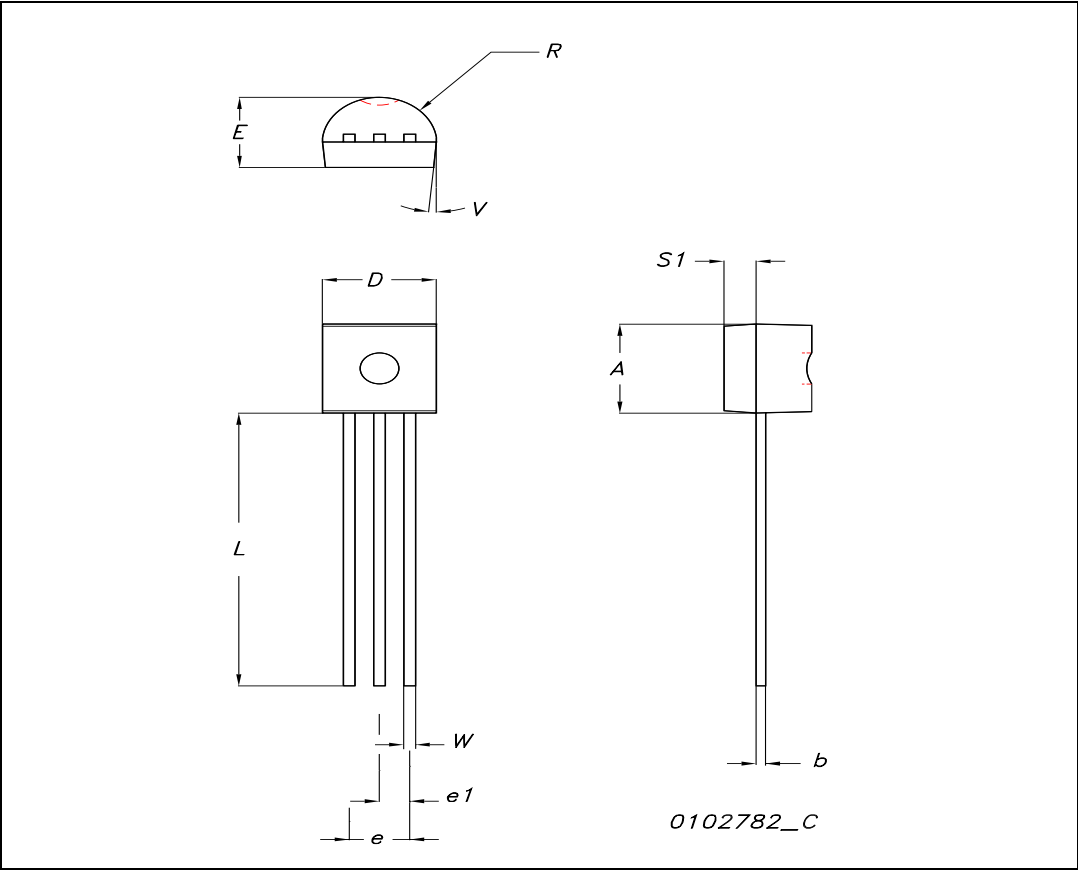
TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°

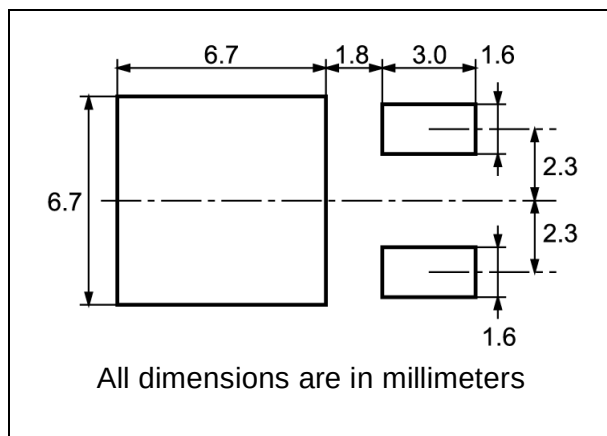


TO-92 MECHANICAL DATA

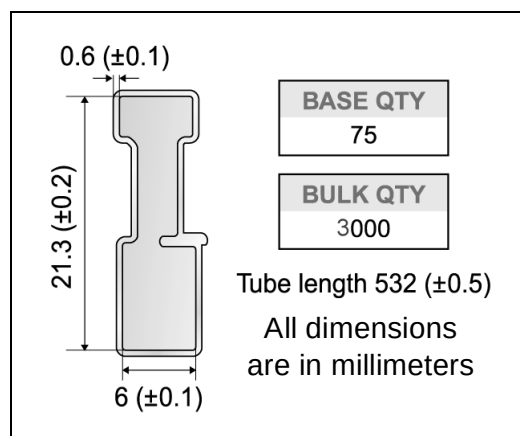
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.32		4.95	0.170		0.194
b	0.36		0.51	0.014		0.020
D	4.45		4.95	0.175		0.194
E	3.30		3.94	0.130		0.155
e	2.41		2.67	0.094		0.105
e1	1.14		1.40	0.044		0.055
L	12.70		15.49	0.50		0.610
R	2.16		2.41	0.085		0.094
S1	0.92		1.52	0.036		0.060
W	0.41		0.56	0.016		0.022
V		5°			5°	



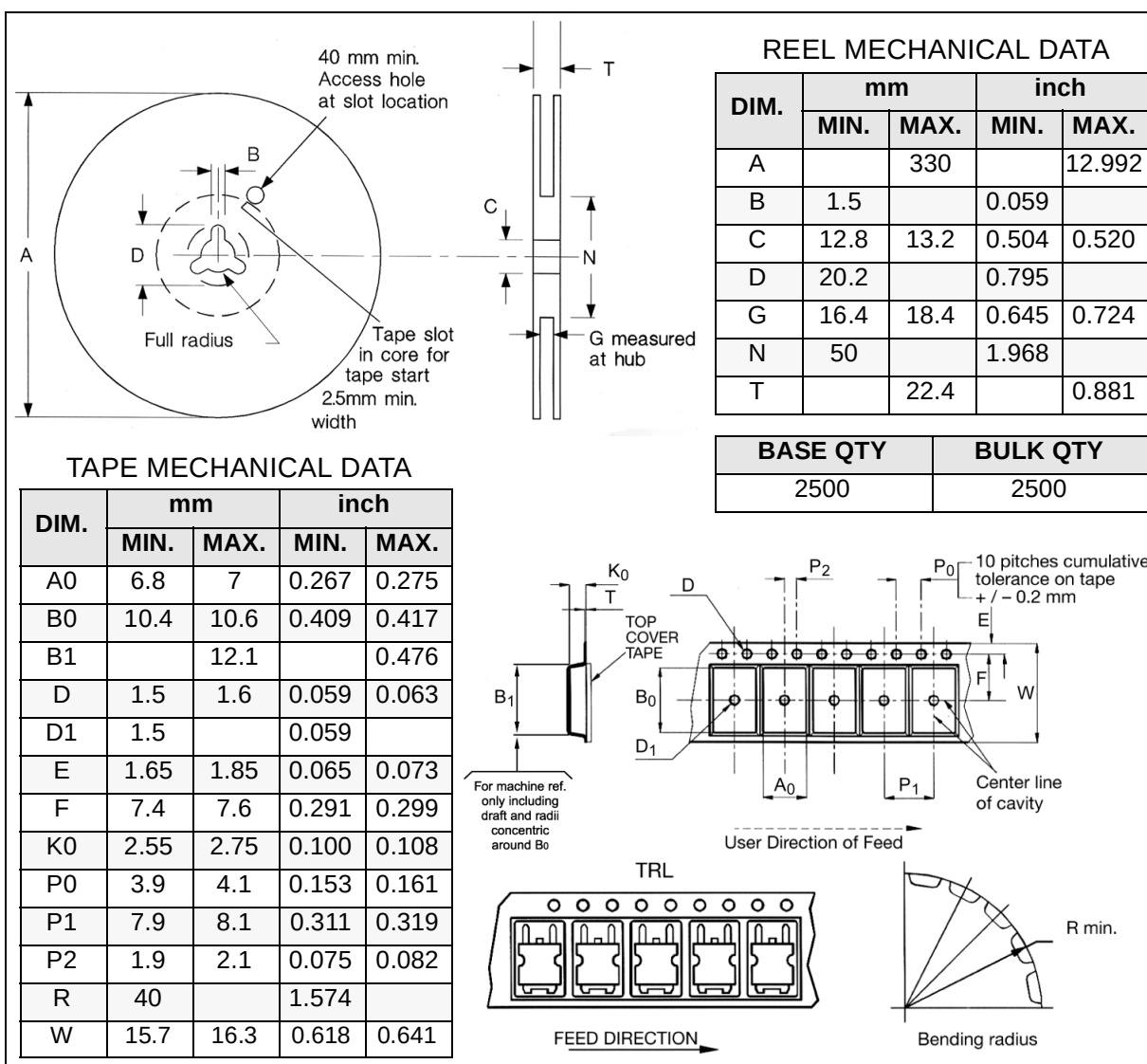
DPAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*

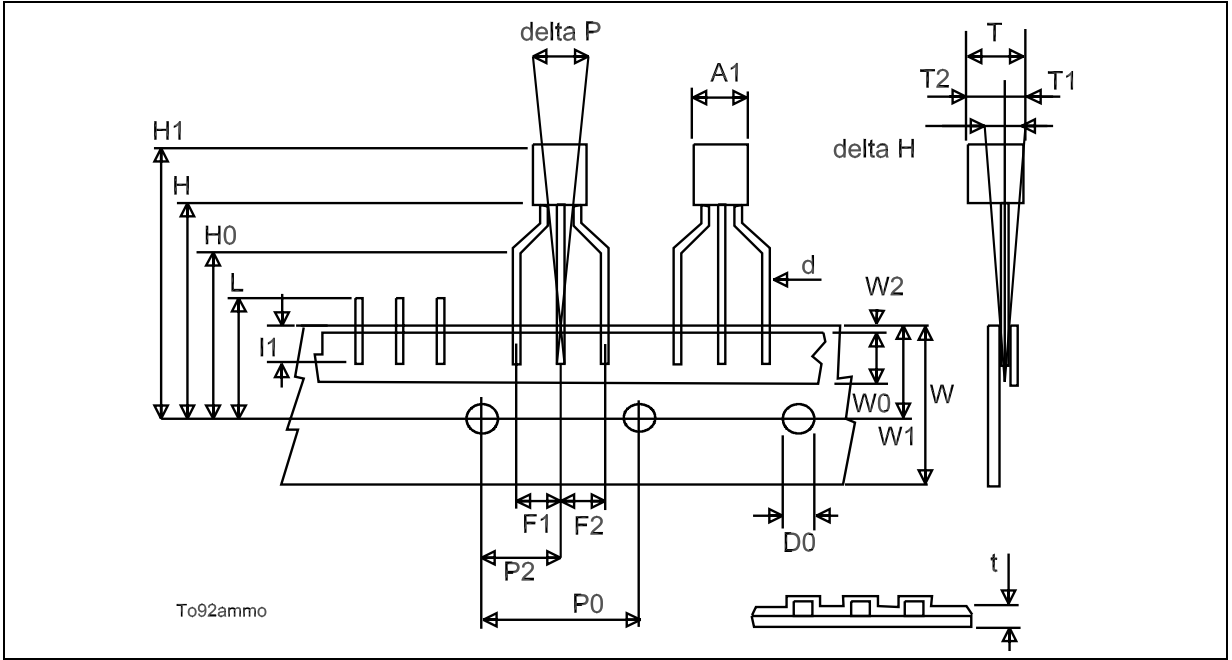


* on sales type



TO-92 AMMOPACK

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A1			4.8			0.19
T			3.8			0.15
T1			1.6			0.06
T2			2.3			0.09
d	0.458		0.505	0.018		0.02
P0	12.5	12.7	12.9	0.49	0.5	0.51
P2	5.65	6.35	7.05	0.22	0.25	0.27
F1, F2	2.44	2.54	2.94	0.09	0.1	0.11
delta H	-2		2	-0.08		0.08
W	17.5	18	19	0.69	0.71	0.74
W0	5.7	6	6.3	0.22	0.23	0.24
W1	8.5	9	9.25	0.33	0.35	0.36
W2			0.5			0.02
H	18.5		20.5	0.72		0.80
H0	15.5	16	16.5	0.61	0.63	0.65
H1			25			0.98
D0	3.8	4	4.2	0.15	0.157	0.16
t			0.9			0.035
L			11			0.43
I1	3			0.11		
delta P	-1		1	-0.04		0.04



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